AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings of claims in the application:

1. (original) A complementary MISFET comprising:

a first linear body including an N-type MISFET and a second linear body including a P-type MISFET; and

a separation region arranged between said first linear body and said second linear body.

2. (original) The complementary MISFET of claim 1, wherein each cross section having a plurality of regions for forming said MISFET is continuously or intermittently formed in the longitudinal direction.

3.(currently amended) The complementary MISFET of claim 1 [[or 2]], wherein said linear bodies and/or said separation region are formed of a material made of an organic semiconductor or electroconductive polymer.

4.(currently amended) An integrated circuit comprising the complementary MISFET of ~~any one of claims 1 through 3~~ claim 1.

5.(currently amended) A production method of the complementary MISFET of ~~any one of claims 1 through 3~~ claim 1, the method comprising the step of:

forming the separation region by coating or vapor depositing an insulating material between the plurality of linear bodies.

6. (currently amended) A production method of the complementary MISFET of ~~any one of claims 1 through 3~~ claim 1, the method comprising the step of:

forming an insulating film on a surface of the linear body to thereby form the separation region.

7.(original) An integrated circuit comprising:

a plurality of linear bodies, each having a cross section which has a plurality of regions for forming a circuit element formed in said linear body and which is continuously or intermittently formed in the longitudinal direction.

8.(original) The integrated circuit of claim 7, wherein said integrated circuit is a semiconductor memory, an image sensor, or a PLA.

9. (currently amended) The integrated circuit of claim 7 [[or 8]], wherein said linear bodies are formed of a material made of an organic semiconductor or electroconductive polymer.

10. (currently amended) The integrated circuit of ~~any one of claims 4 and 7 through 9~~ claim 4, wherein said linear body has a cross section in a circular, polygonal, star, crescent, petal, character shape, or another arbitrary shape.

11. (new) The complementary MISFET of claim 2, wherein said linear bodies and/or said separation region are formed of a material made of an organic semiconductor or electroconductive polymer.

12. (new) An integrated circuit comprising the complementary MISFET of claim 2.

13. (new) An integrated circuit comprising the complementary MISFET of claim 3.

14. (new) A production method of the complementary MISFET of claim 2, the method comprising the step of:

forming the separation region by coating or vapor depositing an insulating material between the plurality of linear bodies.

15. (new) A production method of the complementary MISFET of claim 3, the method comprising the step of:

forming the separation region by coating or vapor depositing an insulating material between the plurality of linear bodies.

16. (new) A production method of the complementary MISFET of claim 2, the method comprising the step of:

forming an insulating film on a surface of the linear body to thereby form the separation region.

17. (new) A production method of the complementary MISFET of claim 3, the method comprising the step of:

forming an insulating film on a surface of the linear body to thereby form the separation region.

18. (new) The integrated circuit of claim 8, wherein said linear bodies are formed of a material made of an organic semiconductor or electroconductive polymer.

19. (new) The integrated circuit of claim 7, wherein said linear body has a cross section in a circular, polygonal, star, crescent, petal, character shape, or another arbitrary shape.

20. (new) The integrated circuit of claim 8, wherein said linear body has a cross section in a circular, polygonal, star, crescent, petal, character shape, or another arbitrary shape.